## *OptiMOS*™3 Power-Transistor

Features

• N-channel, normal level

• Excellent gate charge x $R_{DS(on)}$ product (FOM)

• Very low on-resistance $R_{DS(on)}$

• 175 °C operating temperature

• Pb-free lead plating; RoHS compliant

• Qualified according to JEDEC[1] for target application

• Ideal for high-frequency switching and synchronous rectification

• Halogen-free according to IEC61249-2-21

Product Summary

V_{DS}	120	V
$R_{DS(on),max}$	14.7	mΩ
I_D	56	A

Type	IPB144N12N3 G	IPI147N12N3 G	IPP147N12N3 G
Package	PG-TO263-3	PG-TO262-3	PG-TO220-3
Marking	144N12N	147N12N	147N12N
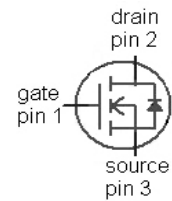
Maximum ratings, at T_j=25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	T_A=25 °C, R_{thJA}=45 K/W	56	A
		T_C=100 °C	41	
Pulsed drain current[2]	$I_{D,pulse}$	I_D=56 A, V_{DS}=80 V, di/dt=100 A/µs, $T_{j,max}$=175 °C	224	
Avalanche energy, single pulse	E_{AS}	I_D=56 A, R_{GS}=25 Ω	90	mJ
Gate source voltage[3]	V_{GS}		±20	V
Power dissipation	P_{tot}	T_C=25 °C	107	W
Operating and storage temperature	T_j, T_{stg}		-55 ... 175	°C
IEC climatic category; DIN IEC 68-1			55/175/56	

[1] J-STD20 and JESD22

[2] see figure 3

[3] T_{jmax}=150°C and duty cycle D=0.01 for Vgs<-5V

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Thermal characteristics

Parameter	Symbol	Conditions	min.	typ.	max.	Unit
Thermal resistance, junction - case	R_{thJC}		-	-	1.4	K/W
Thermal resistance, junction - ambient	R_{thJA}	minimal footprint	-	-	62	
		6 cm2 cooling area[4]	-	-	40	

Electrical characteristics, at T_j=25 °C, unless otherwise specified

Static characteristics

Parameter	Symbol	Conditions	min.	typ.	max.	Unit
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS}=0 V, I_D=1 mA	120	-	-	V
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=61 µA	2	3	4	
Zero gate voltage drain current	I_{DSS}	V_{DS}=100 V, V_{GS}=0 V, T_j=25 °C	-	0.1	1	µA
		V_{DS}=100 V, V_{GS}=0 V, T_j=125 °C	-	10	100	
Gate-source leakage current	I_{GSS}	V_{GS}=20 V, V_{DS}=0 V	-	1	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=10 V, I_D=56 A, (TO263)	-	12.3	14.4	mΩ
		V_{GS}=10 V, I_D=56 A, (TO220, TO262)	-	12.6	14.7	
Gate resistance	R_G		-	1.2	-	Ω
Transconductance	g_{fs}	$\lvert V_{DS}\rvert$>2$\lvert I_D\rvert R_{DS(on)max}$, I_D=56 A	31	62	-	S

[4] Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm^2 (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Dynamic characteristics						
Input capacitance	C_{iss}	V_{GS}=0 V, V_{DS}=60 V, f=1 MHz	-	2420	3220	pF
Output capacitance	C_{oss}		-	304	404	
Reverse transfer capacitance	C_{rss}		-	17	-	
Turn-on delay time	$t_{d(on)}$	V_{DD}=60 V, V_{GS}=10 V, I_D=56 A, R_G=1.6 Ω	-	16	-	ns
Rise time	t_r		-	9	-	
Turn-off delay time	$t_{d(off)}$		-	24	-	
Fall time	t_f		-	4	-	

Gate Charge Characteristics[5]

| Parameter	Symbol	Conditions	Values			Unit
Gate to source charge	Q_{gs}	V_{DD}=60 V, I_D=56 A, V_{GS}=0 to 10 V	-	13	-	nC
Gate to drain charge	Q_{gd}		-	9	-	
Switching charge	Q_{sw}		-	15	-	
Gate charge total	Q_g		-	37	49	
Gate plateau voltage	$V_{plateau}$		-	5.5	-	V
Output charge	Q_{oss}	V_{DD}=60 V, V_{GS}=0 V	-	42	55	nC

| Parameter	Symbol	Conditions	Values			Unit
Reverse Diode						
Diode continous forward current	I_S	T_C=25 °C	-	-	56	A
Diode pulse current	$I_{S,pulse}$		-	-	224	
Diode forward voltage	V_{SD}	V_{GS}=0 V, I_F=56 A, T_j=25 °C	-	1	1.2	V
Reverse recovery time	t_{rr}	V_R=60 V, I_F=I_S, di_F/dt=100 A/µs	-	91		ns
Reverse recovery charge	Q_{rr}		-	259	-	nC

[5] See figure 16 for gate charge parameter definition

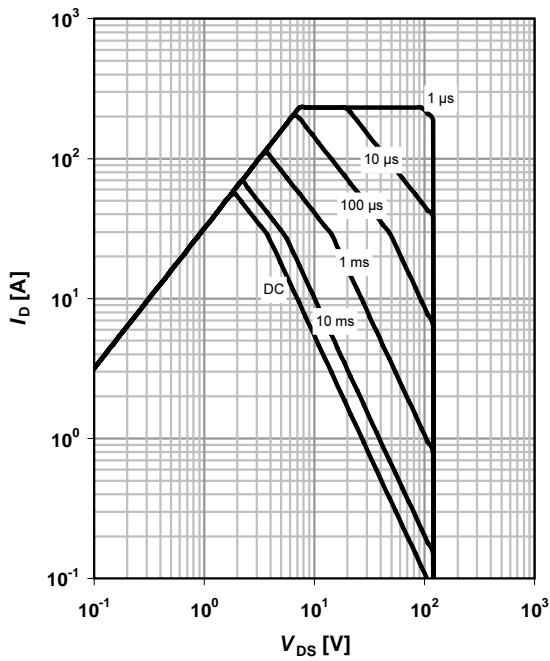**1 Power dissipation**

P_{tot}=f(T_C)
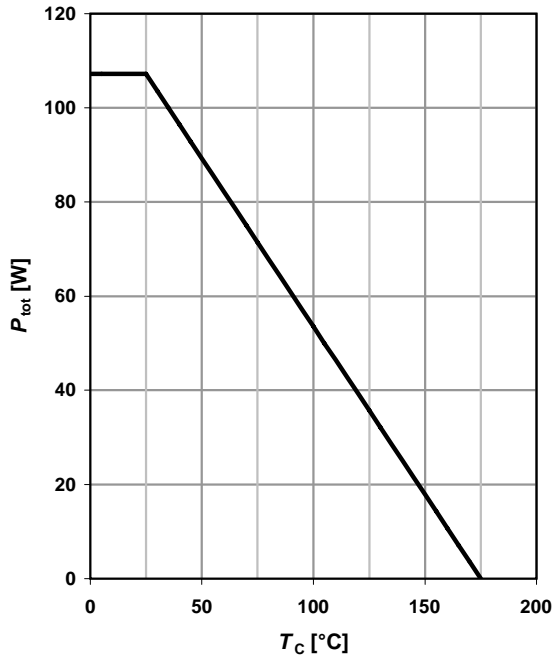
2 Drain current

I_D=f(T_C); V_{GS}≥10 V
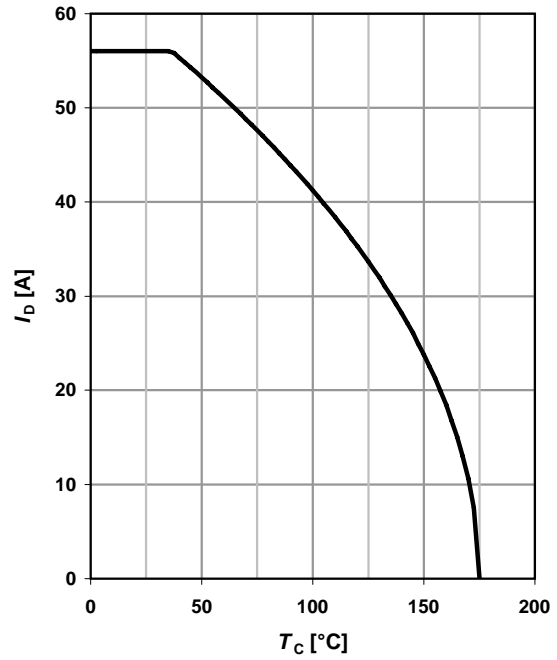
3 Safe operating area
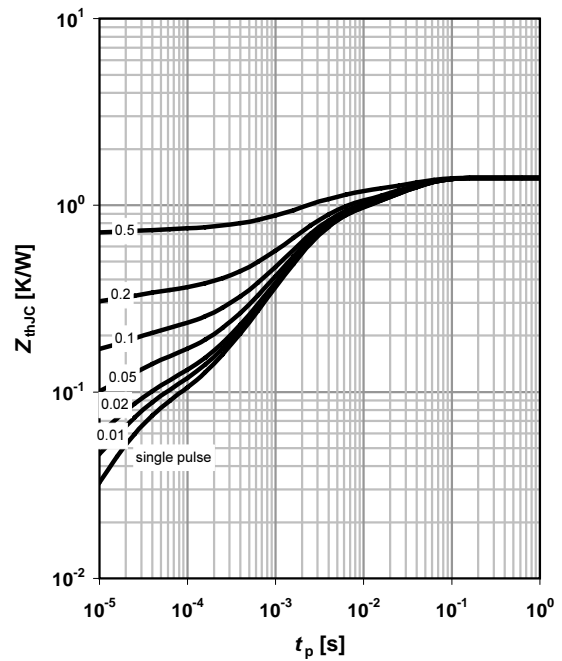
I_D=f(V_{DS}); T_C=25 °C; D=0

parameter: t_p
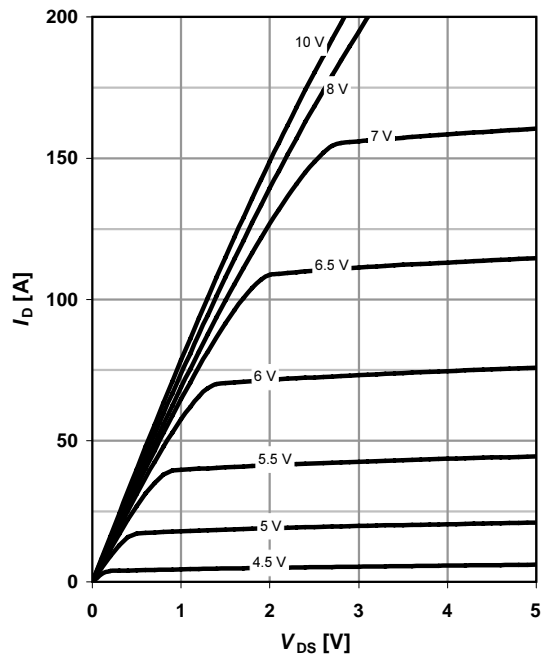
4 Max. transient thermal impedance

Z_{thJC}=f(t_p)

parameter: D=t_p/T
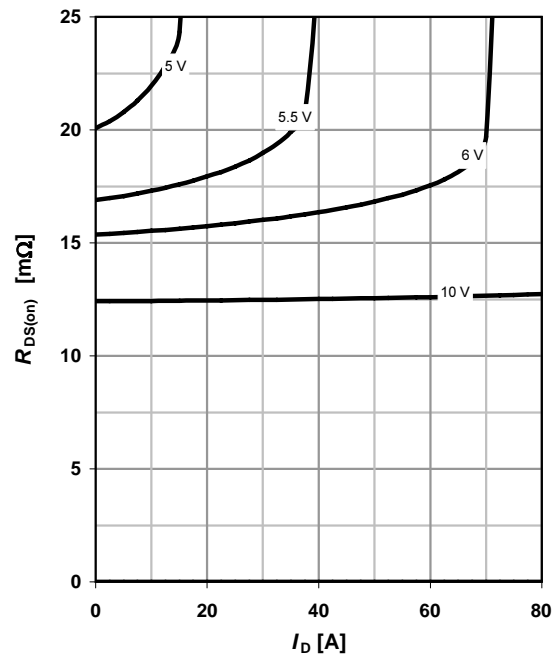
5 Typ. output characteristics

I_D=f(V_{DS}); T_j=25 °C

parameter: V_{GS}

6 Typ. drain-source on resistance

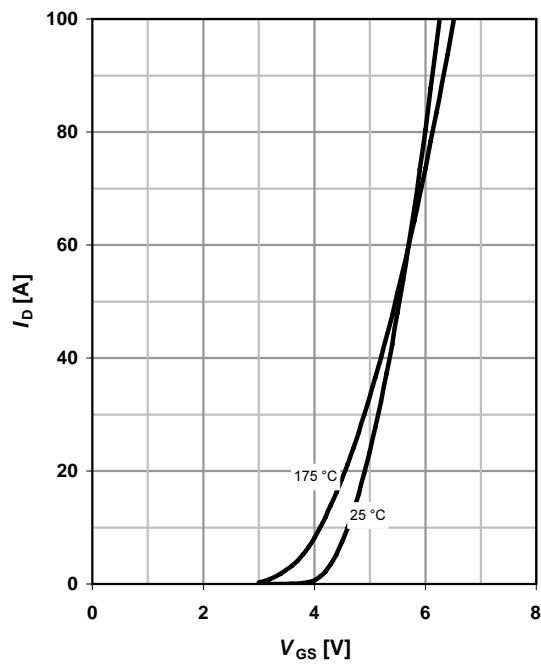$R_{DS(on)}$=f(I_D); T_j=25 °C

parameter: V_{GS}

7 Typ. transfer characteristics

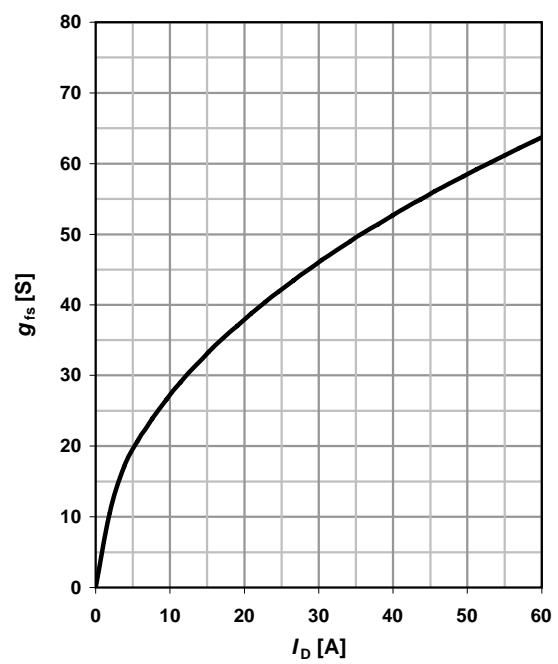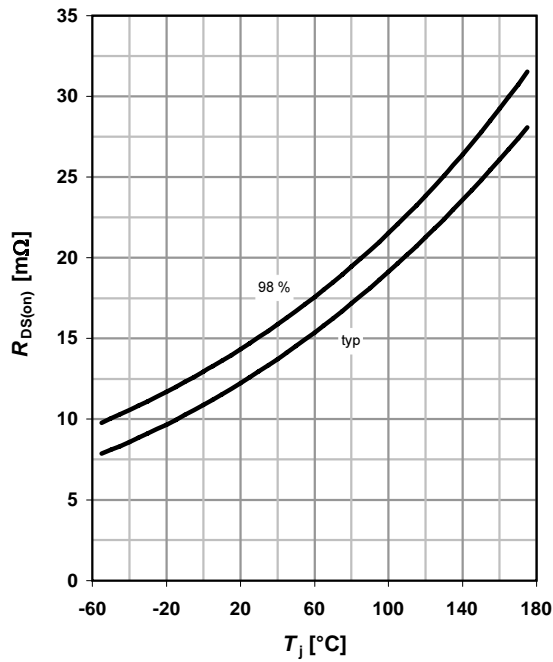I_D=f(V_{GS}); $|V_{DS}|$>2$|I_D|R_{DS(on)max}$

parameter: T_j

8 Typ. forward transconductance

g_{fs}=f(I_D); T_j=25 °C

9 Drain-source on-state resistance

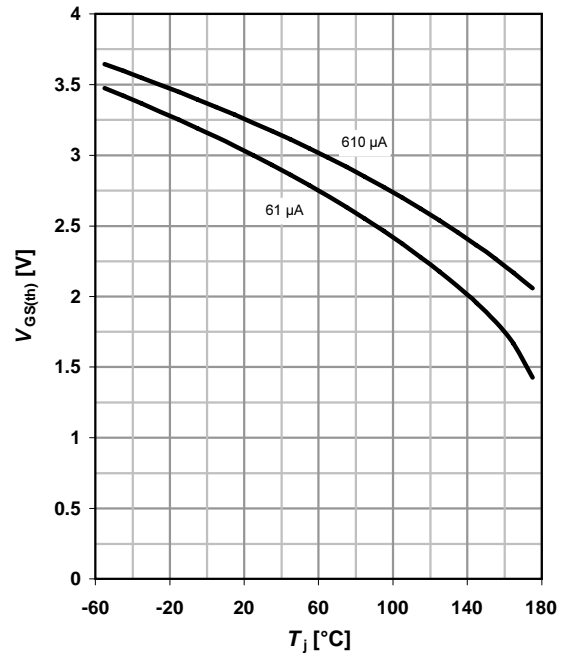$R_{DS(on)}$=f(T_j); I_D=56 A; V_{GS}=10 V

10 Typ. gate threshold voltage
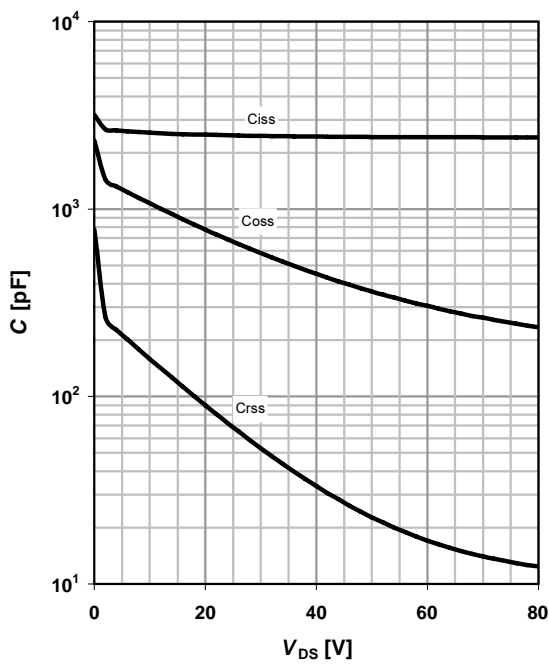
$V_{GS(th)}$=f(T_j); V_{GS}=V_{DS}
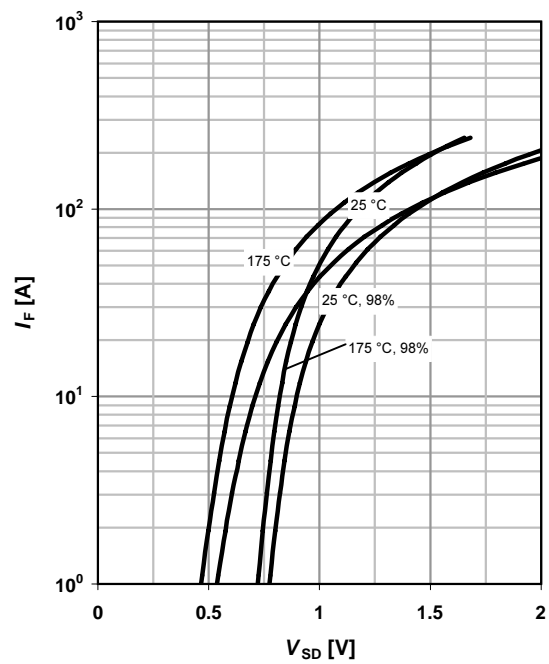
parameter: I_D

11 Typ. capacitances

C=f(V_{DS}); V_{GS}=0 V; f=1 MHz

12 Forward characteristics of reverse diode
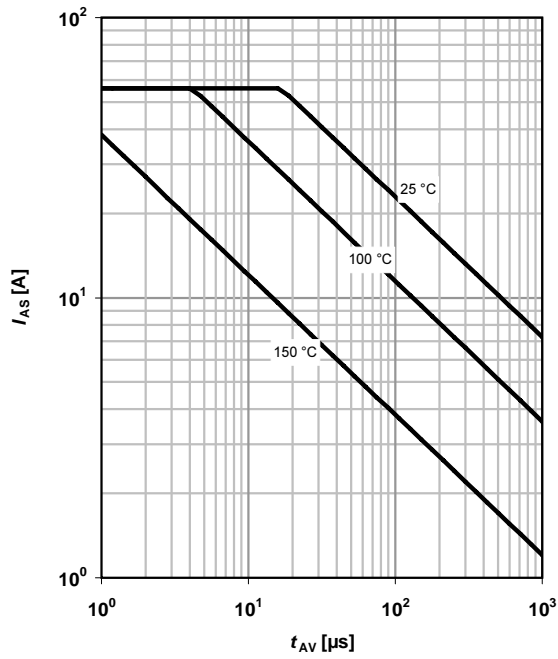
I_F=f(V_{SD})

parameter: T_j

13 Avalanche characteristics

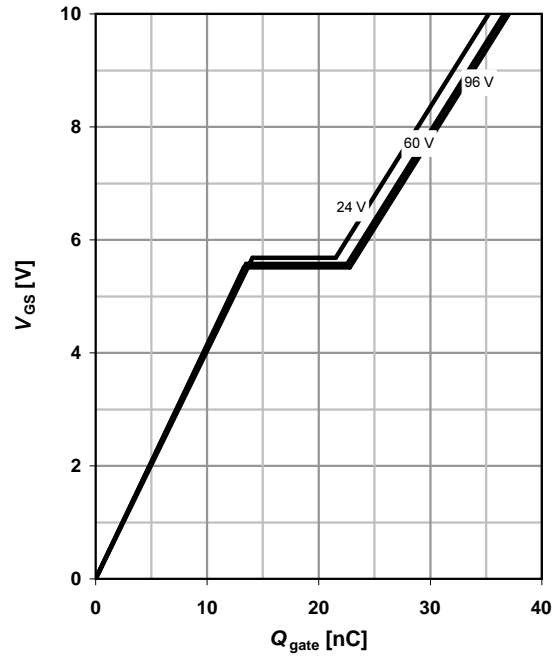I_{AS}=f(t_{AV}); R_{GS}=25 Ω
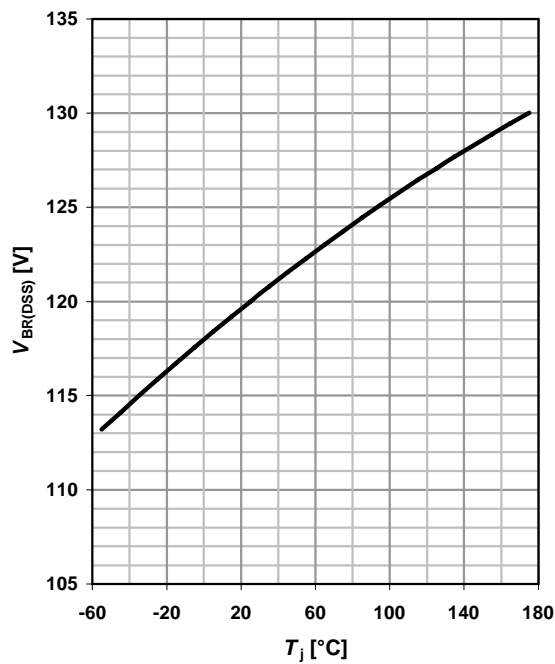
parameter: $T_{j(start)}$

14 Typ. gate charge

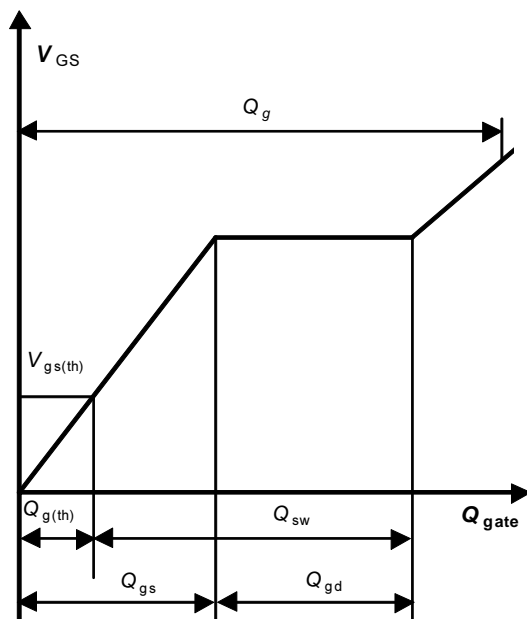V_{GS}=f(Q_{gate}); I_D=56 A pulsed

parameter: V_{DD}

15 Drain-source breakdown voltage

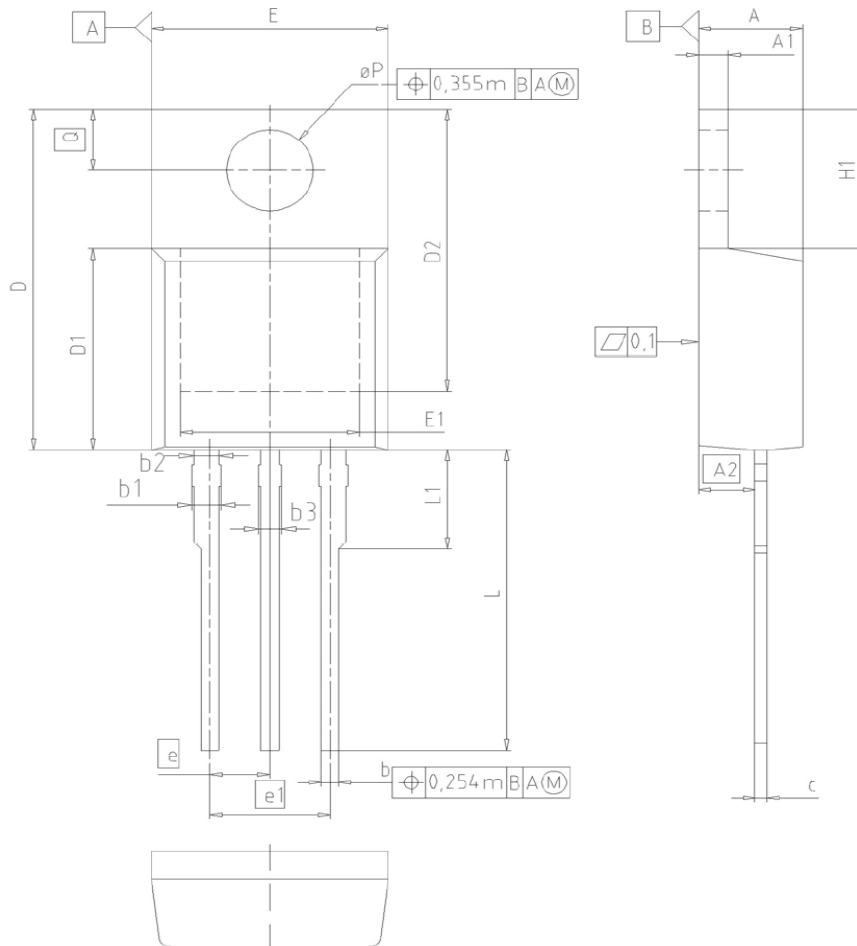$V_{BR(DSS)}$=f(T_j); I_D=1 mA

16 Gate charge waveforms

PG-TO220-3: Outline

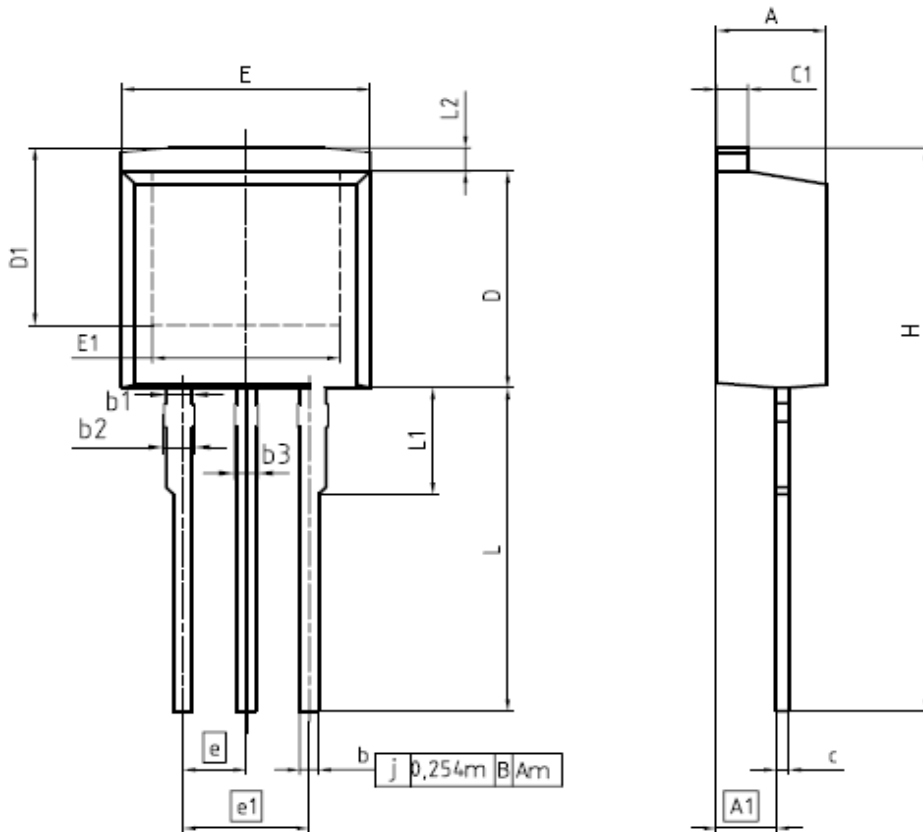| DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.57	0.169	0.180
A1	1.17	1.40	0.046	0.055
A2	2.15	2.72	0.085	0.107
b	0.65	0.86	0.026	0.034
b1	0.95	1.40	0.037	0.055
b2	0.95	1.15	0.037	0.045
b3	0.65	1.15	0.026	0.045
c	0.33	0.60	0.013	0.024
D	14.81	15.95	0.583	0.628
D1	8.51	9.45	0.335	0.372
D2	12.19	13.10	0.480	0.516
E	9.70	10.36	0.382	0.408
E1	6.50	8.60	0.256	0.339
e	2.54		0.100	
e1	5.08		0.200	
N	3		3	
H1	5.90	6.90	0.232	0.272
L	13.00	14.00	0.512	0.551
L1	-	4.80	-	0.189
øP	3.60	3.89	0.142	0.153
Q	2.60	3.00	0.102	0.118

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EUROPEAN PROJECTION

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05

PG-TO262-3-1 (I²PAK)

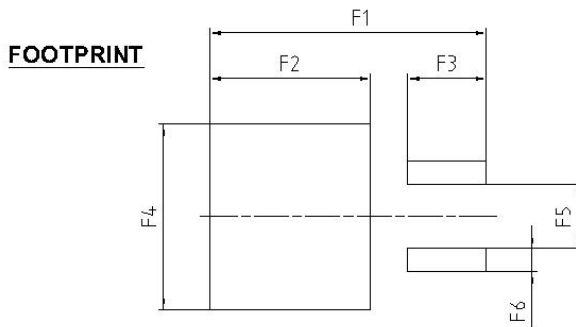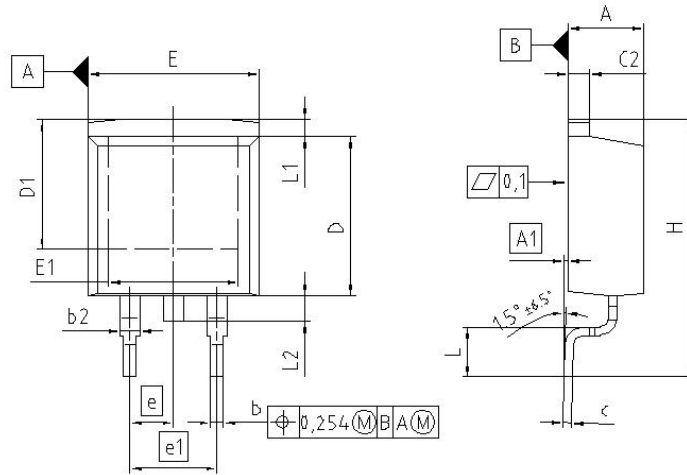| DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4,300	4,572	0,169	0,180
A1	2,150	2,718	0,085	0,107
b	0,650	0,864	0,026	0,034
b1	0,950	1,093	0,037	0,043
b2	0,950	1,400	0,037	0,055
b3	0,650	1,118	0,026	0,044
c	0,330	0,600	0,013	0,024
c1	1,170	1,400	0,046	0,055
D	8,509	9,450	0,335	0,372
D1	6,900	-	0,272	-
E	9,700	10,363	0,382	0,408
E1	6,500	8,600	0,256	0,339
e	2,540		0,100	
e1	5,080		0,200	
N	3		3	
L	13,000	14,000	0,512	0,551
L1	-	4,800	-	0,189
L2	-	1,727	-	0,068

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JEDEC TO262

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FILE
TO262_1

PG-TO-263 (D²-Pak)

FOOTPRINT

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.300	4.572	0.169	0.180
A1	0.000	0.254	0.000	0.010
b	0.650	0.850	0.026	0.033
b2	0.950	1.321	0.037	0.052
c	0.330	0.650	0.013	0.026
c2	0.170	1.400	0.046	0.055
D	8.509	9.450	0.335	0.372
D1	7.100	-	0.280	-
E	9.800	10.312	0.386	0.406
E1	6.500		0.256	
e	2.540		0.100	
e1	5.080		0.200	
N	2		2	
H	14.605	15.875	0.575	0.625
L	2.200	3.000	0.087	0.118
L1	-	1.600	-	0.063
L2	1.000	1.778	0.039	0.070
F1	16.050	16.250	0.632	0.640
F2	9.300	9.500	0.366	0.374
F3	4.500	4.700	0.177	0.185
F4	10.700	10.900	0.421	0.429
F5	3.630	3.830	0.143	0.151
F6	1.100	1.300	0.043	0.051

REFERENCE
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SCALE

7.5mm

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